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NIP-154 2-700

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

M. IZAWA et al

Serial No. 09/373723

Filed: August 13, 1999

For: A DRY ETCHING METHOD

PRELIMINARY AMENDMENT

Assistant Commissioner of Patents
Washington, D.C. 20231

Sir:

Prior to the examination thereof, please amend the above-identified patent application as follows.

IN THE CLAIMS

Please amend claims 21 and 22 as follows.

21. (Amended) A dry etching method as claimed in [any one of] claim[s] 1 [to 15, 17 and 19], wherein

said magnetic field gradient in said electron-cyclotron resonance (ECR) region is set so that a ratio of magnetic field gradient/magnetic field intensity is in the range from 0.15/cm to 0.01/cm.

22. (Amended) A dry etching method as claimed in [any one of] claim[s] 1 [to 21], wherein

high frequency bias of 400 kHz to 13.56 MHz is applied to said process platform for wafer.